TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

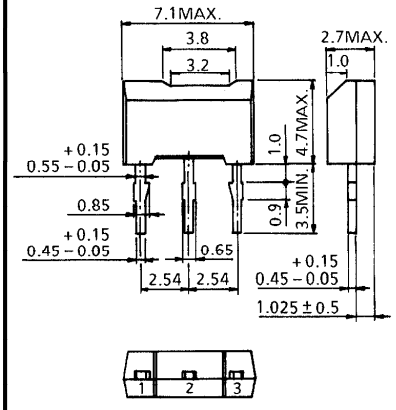
2SC3671

STOROBE FLASH APPLICATIONS

MEDIUM POWER AMPLIFIER APPLICATIONS

- High DC Current Gain and Excellent h_{FE} Linearity
  : $h_{FE\,(1)}$ = 140~450
  : $h_{FE\,(2)}$ = 70 (Min.)
- Low Saturation Voltage : $V_{CE\,(sat)}$ = 1.0V (Max.)

Unit in mm



1. BASE
2. COLLECTOR
3. EMITTER

JEDEC	—
EIAJ	—
TOSHIBA	2-7D101A

Weight : 0.2g (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	50	V
Collector-Emitter Voltage		V_{CES}	40	V
		V_{CEO}	20	
Emitter-Base Voltage		V_{EBO}	8	V
Collector Current	DC	I_C	5	A
	Pulse (Note 1)	I_{CP}	8	
Base Current		I_B	0.5	A
Collector Power Dissipation		P_C	1000	mW
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

Note 1 : Pulse Width ≦ 10ms, Duty Cycle ≦ 30%

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB} = 40V, I_E = 0	—	—	100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 8V, I_C = 0	—	—	100	nA
Collector-Emitter Breakdown Voltage	V_{CEO}	I_C = 10mA, I_B = 0	20	—	—	V
Emitter-Base Breakdown Voltage	V_{EBO}	I_E = 1mA, I_C = 0	8	—	—	V
DC Current Gain	$h_{FE\,(1)}$ (Note 2)	V_{CE} = 2V, I_C = 0.5A	140	—	450	
	$h_{FE\,(2)}$	V_{CE} = 2V, I_C = 4A	70	—	—	
Collector-Emitter Saturation Voltage	$V_{CE\,(sat)}$	I_C = 4A, I_B = 0.1A	—	—	1.0	V
Base-Emitter Voltage	V_{BE}	V_{CE} = 2V, I_C = 4A	—	—	1.5	V
Transition Frequency	f_T	V_{CE} = 2V, I_C = 0.5A	—	100	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	—	40	—	pF

Note 2 : $h_{FE\,(1)}$ Classification A : 140~240, B : 200~330, C : 300~450

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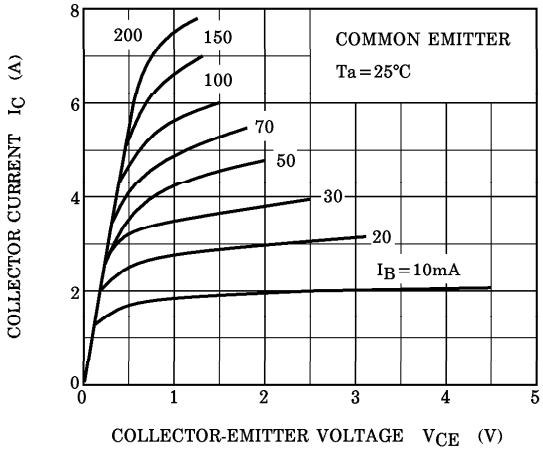
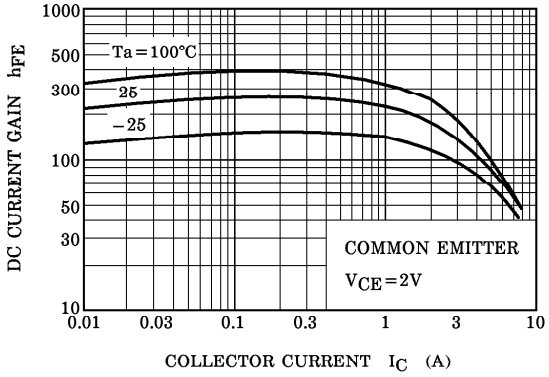
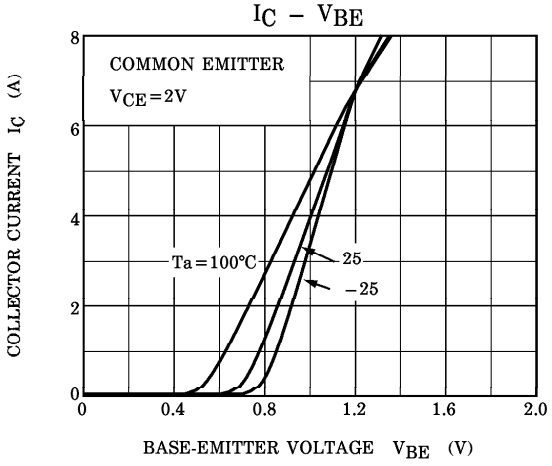
I_C – V_{BE}



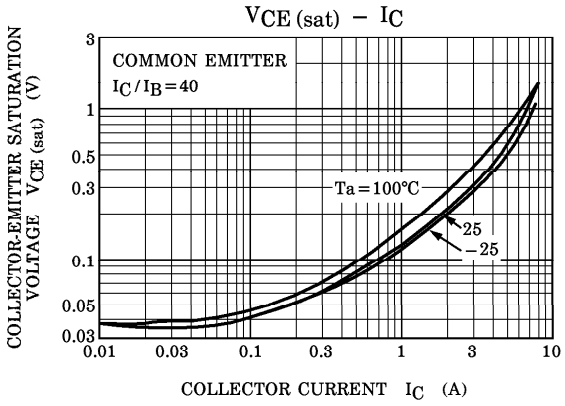
h_{FE} – I_C



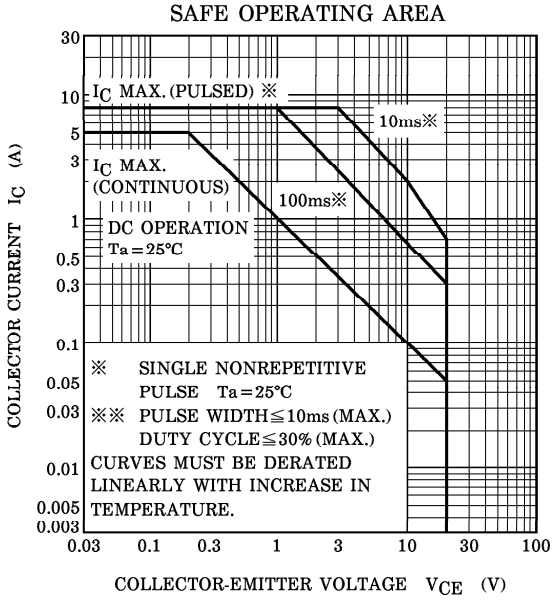
I_C – V_{BE}



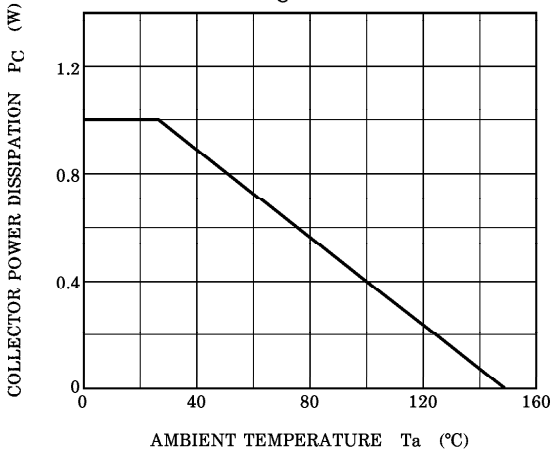
$V_{CE\,(sat)}$ – I_C



SAFE OPERATING AREA



P_C – Ta



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